Please add new claims 78-157 as follows:

--78. A semiconductor device for electro-optical device comprising a CMOS device comprising n-channel and p-channel TFTs, each of said n-channel and p-channel TFTs comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween; and

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween,

wherein the source and the drain regions have at least one portion containing one or more elements selected from the group consisting of carbon, nitrogen, and oxygen at a concentration of 1×10^{19} atoms/cm^3 or more.

~~79. A device according to claim 78 wherein said semiconductor device comprises~~ transistors selected from the group of a stagger type, ~~an inverted~~ stagger type, a planar type, and ~~an inverted~~ planar type transistors.

80. A device according to claim 78 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

81. A device according to claim 80 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

82. A device according to claim 78 wherein said channel region comprises boron at a concentration of from 1×10^{15} to ~~5×10^{17}~~ atoms/cm^3.

83. A device according to clam 78 wherein portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

84. A semiconductor device for electro-optical device comprising a CMOS device comprising n-channel and p-channel TFTs, each of said n-channel and p-channel TFTs comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween; and

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween,

wherein the source and the drain regions have at least one portion containing carbon at a concentration of 1×10^{19} atoms/cm^3 or more.

85. A device according to claim 84 ~~wherein said semiconductor device comprises~~ transistors selected ~~from~~ the group of a stagger type, an inverted stagger type, a planar ~~type~~, and an inverted planar type transistors.

86. A device according to claim 84 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

87. A device according to claim 86 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

88. A device according to claim 84 wherein said channel region comprises boron at a concentration of from 1 x 10^{15} to 5 x 10^{17} atoms/cm^3.

89. A device according to clam 84 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

90. A semiconductor device for electro-optical device comprising a CMOS device comprising n-channel and p-channel TFTs, each of said n-channel and p-channel TFTs comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween; and

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween,

wherein the source and the drain regions have at least one portion containing nitrogen at a concentration of 1 x 10^{19} atoms/cm^3 or more.

91. A device according to claim 90 wherein said semiconductor device comprises transistors selected from the group of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

92. A device according to claim 90 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

93. A device according to claim 92 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

94. A device according to claim 90 wherein said channel region comprises boron at a concentration of from 1 x 10^{15} to 5 x 10^{17} atoms/cm^3.

95. A device according to clam 90 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

96. A semiconductor device for electro-optical device comprising a CMOS device comprising n-channel and p-channel TFTs, each of said n-channel and p-channel TFTs comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween; and

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween,

wherein the source and the drain regions have at least one portion containing oxygen at a concentration of 1 x 10^{19} atoms/cm^3 or more.

97. A device according to claim 96 wherein said semiconductor device comprises transistors selected from the group of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

98. A device according to claim 96 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

99. A device according to claim 98 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

100. A device according to claim 96 wherein said channel region comprises boron at a concentration of from 1 x 10^{15} to 5 x 10^{17} atoms/cm^3.

101. A device according to clam 96 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

102. A semiconductor device for electro-optical device comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween; and

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween,

wherein said channel region has least one portion containing one or more elements selected from the group consisting of carbon, nitrogen, and oxygen at a concentration of 1 x 10^{19} atoms/cm^3 or more.

103. A device according to claim 102 wherein said semiconductor layer is included in both n-channel and p-channel TFTs in a CMOS device of said electro-optical device.

104. A device according to claim 102 further comprising:

a first interlayer insulating film over said semiconductor layer and said gate electrode, said first interlayer insulating film comprising inorganic material;

a second interlayer insulating film on said first interlayer insulating film, said second interlayer insulating film comprising organic resin; and

a pixel electrode on said second interlayer insulating film,

wherein said electro-optical device is a transparent type or a reflective type device.

105. A device according to claim 102 wherein said semiconductor device comprises transistors selected from the group of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

106. A device according to claim 102 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

107. A device according to claim 106 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

108. A device according to claim 102 wherein said channel region comprises boron at a concentration of from 1×10^{15} to 5×10^{17} atoms/cm^3.

109. A device according to clam 102 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

110. A semiconductor device for electro-optical device comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween; and

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween,

wherein said channel region has least one portion containing carbon at a concentration of 1×10^{19} atoms/cm^3 or more.

111. A device according to claim 110 wherein said semiconductor layer is included in both n-channel and p-channel TFTs in a CMOS device of said electro-optical device.

112. A device according to claim 110 further comprising:

a first interlayer insulating film over said semiconductor layer and said gate electrode, said first interlayer insulating film comprising inorganic material;

a second interlayer insulating film on said first interlayer insulating film, said second interlayer insulating film comprising organic resin; and

a pixel electrode on said second interlayer insulating film,

wherein said electro-optical device is a transparent type or a reflective type device.

113. A device according to claim 110 ~~wherein said semiconductor device~~ comprises ~~transistors selected~~ from the group of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

114. A device according to claim 110 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

115. A device according to claim 114 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

116. A device according to claim 110 wherein said channel region comprises boron at a concentration of from 1×10^{15} to 5×10^{17} atoms/cm^3.

117. A device according to claim 110 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

118. A semiconductor device for electro-optical device comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween; and

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween,

wherein said channel region has least one portion containing nitrogen at a concentration of 1×10^{19} atoms/cm^3 or more.

119. A device according to claim 118 wherein said semiconductor layer is included in both n-channel and p-channel TFTs in a CMOS device of said electro-optical device.

120. A device according to claim 118 further comprising:

a first interlayer insulating film over said semiconductor layer and said gate electrode, said first interlayer insulating film comprising inorganic material;

a second interlayer insulating film on said first interlayer insulating film, said second interlayer insulating film comprising organic resin; and

a pixel electrode on said second interlayer insulating film,

wherein said electro-optical device is a transparent type or a reflective type device.

121. A device according to claim 118 wherein said semiconductor device comprises transistors selected from the group of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

122. A device according to claim 118 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

123. A device according to claim 122 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

124. A device according to claim 118 wherein said channel region comprises boron at a concentration of from 1 x 10^{15} to 5 x 10^{17} atoms/cm^3.

125. A device according to clam 118 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

126. A semiconductor device for electro-optical device comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween, and

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween,

wherein said channel region has least one portion containing oxygen at a concentration of 1×10^{19} atoms/cm^3 or more.

127. A device according to claim 126 wherein said semiconductor layer is included in both n-channel and p-channel TFTs in a CMOS device of said electro-optical device.

128. A device according to claim 126 further comprising:

a first interlayer insulating film over said semiconductor layer and said gate electrode, said first interlayer insulating film comprising inorganic material;

a second interlayer insulating film on said first interlayer insulating film, said second interlayer insulating film comprising organic resin; and

a pixel electrode on said second interlayer insulating film,

wherein said electro-optical device is a transparent type or a reflective type device.

~~129. A device according to claim 126 wherein said semiconductor device comprises~~ transistors selected ~~from the group~~ of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

130. A device according to claim 126 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

131. A device according to claim 130 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

132. A device according to claim 126 wherein said channel region comprises boron at a concentration of from 1 x 10^{15} to 5 x 10^{17} atoms/cm^3.

133. A device according to clam 126 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

134. A semiconductor device for electro-optical device comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween;

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween;

a first interlayer insulating film over said semiconductor layer and said gate electrode, said first interlayer insulating film comprising inorganic material;

a second interlayer insulating film on said first interlayer insulating film, said second interlayer insulating film comprising organic resin; and

a pixel electrode on said second interlayer insulating film,

wherein said the source and the drain regions have at least one portion containing one or more elements selected from the group consisting of carbon, nitrogen, and oxygen at a concentration of 1 x 10^{19} atoms/cm^3 or more.

135. A device according to claim 134 wherein said semiconductor device comprises transistors selected from the group of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

136. A device according to claim 134 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

137. A device according to claim 136 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

138. A device according to claim 134 wherein said channel region comprises boron at a concentration of from 1×10^{15} to 5×10^{17} atoms/cm^3.

139. A device according to claim 134 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

140. A semiconductor device for electro-optical device comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween;

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween;

a first interlayer insulating film over said semiconductor layer and said gate electrode, said first interlayer insulating film comprising inorganic material;

a second interlayer insulating film on said first interlayer insulating film, said second interlayer insulating film comprising organic resin; and

a pixel electrode on said second interlayer insulating film,

wherein the source and the drain regions have at least one portion containing carbon at a concentration of 1 x 10^{19} atoms/cm^3 or more.

141. A device according to claim 140 wherein said semiconductor device comprises transistors selected from the group of a stagger type, an inverted stagger type, a planar type, and an inverted planar type transistors.

142. A device according to claim 140 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

143. A device according to claim 142 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

144. A device according to claim 140 wherein said channel region comprises boron at a concentration of from 1 x 10^{15} to 5 x 10^{17} atoms/cm^3.

145. A device according to claim 140 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

146. A semiconductor device for electro-optical device comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween;

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween;

a first interlayer insulating film over said semiconductor layer and said gate electrode, said first interlayer insulating film comprising inorganic material;

a second interlayer insulating film on said first interlayer insulating film, said second interlayer insulating film comprising organic resin; and

a pixel electrode on said second interlayer insulating film,

wherein the source and the drain regions have at least one portion containing nitrogen at a concentration of 1 x 10^{19} atoms/cm^3 or more.

~~147. A device according to claim 146 wherein said semiconductor device comprises~~ transistors selected from ~~the group of~~ a stagger type, an inverted stagger type, a planar type, ~~and~~ an inverted planar type transistors.

148. A device according to claim 146 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.

149. A device according to claim 148 wherein said non-single crystalline semiconductor comprises one selected from the group consisting of amorphous silicon, polycrystalline silicon, and semi-crystalline silicon.

150. A device according to claim 146 wherein said channel region comprises boron at a concentration of from 1 x 10^{15} to 5 x 10^{17} atoms/cm^3.

151. A device according to claim 146 wherein said portion is located adjacent to a boundary between the source and the channel regions or a boundary between the drain and the channel regions.

152. A semiconductor device for electro-optical device comprising:

a semiconductor layer comprising at least a channel region and source and drain regions with said channel region interposed therebetween;

a gate electrode adjacent to said channel region with a gate insulating film interposed therebetween;

a first interlayer insulating film over said semiconductor layer and said gate electrode, said first interlayer insulating film comprising inorganic material;

a second interlayer insulating film on said first interlayer insulating film, said second interlayer insulating film comprising organic resin; and

a pixel electrode on said second interlayer insulating film,

wherein the source and the drain regions have at least one portion containing oxygen at a concentration of 1×10^{19} atoms/cm^3 or more.

~~153. A device according to claim 152 wherein said semiconductor device comprises~~ transistors selected ~~from the~~ group of a stagger type, an inverted stagger type, a planar ~~type, and~~ an inverted planar type transistors.

154. A device according to claim 152 wherein said semiconductor layer comprises a non-single crystalline semiconductor layer comprising one selected from the group consisting of silicon, germanium, and gallium arsenide.